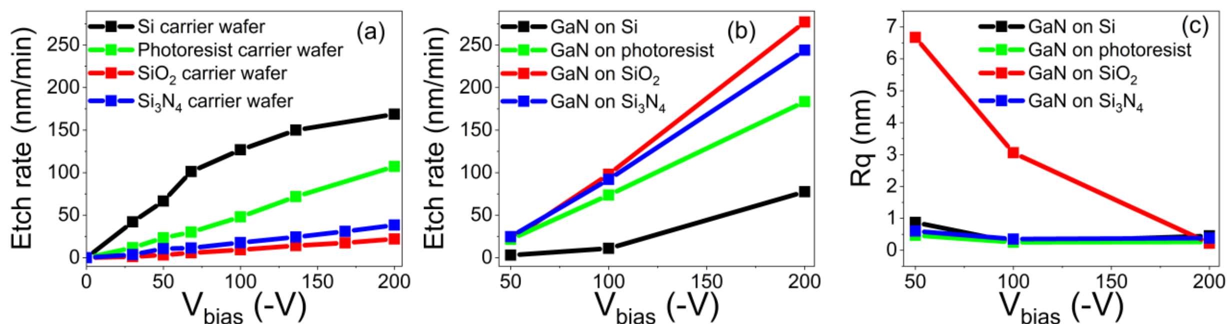

Figure 1. (a) Carrier wafers etch rate (b) GaN etch rate (c) GaN roughness as function of the bias potential after Cl_2 etching.

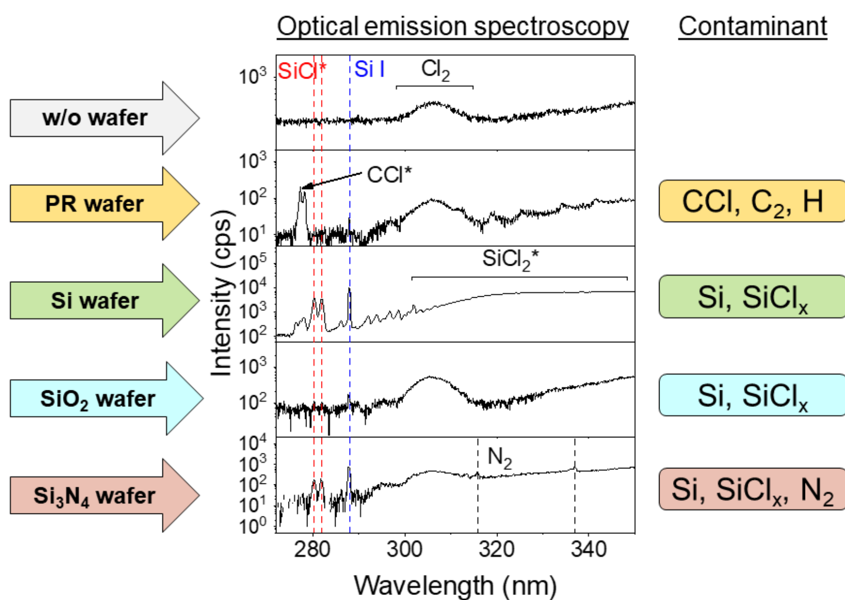

Figure 2. Optical emission spectra recorded during the Cl_2 etching of different carrier wafers at - 200 V.

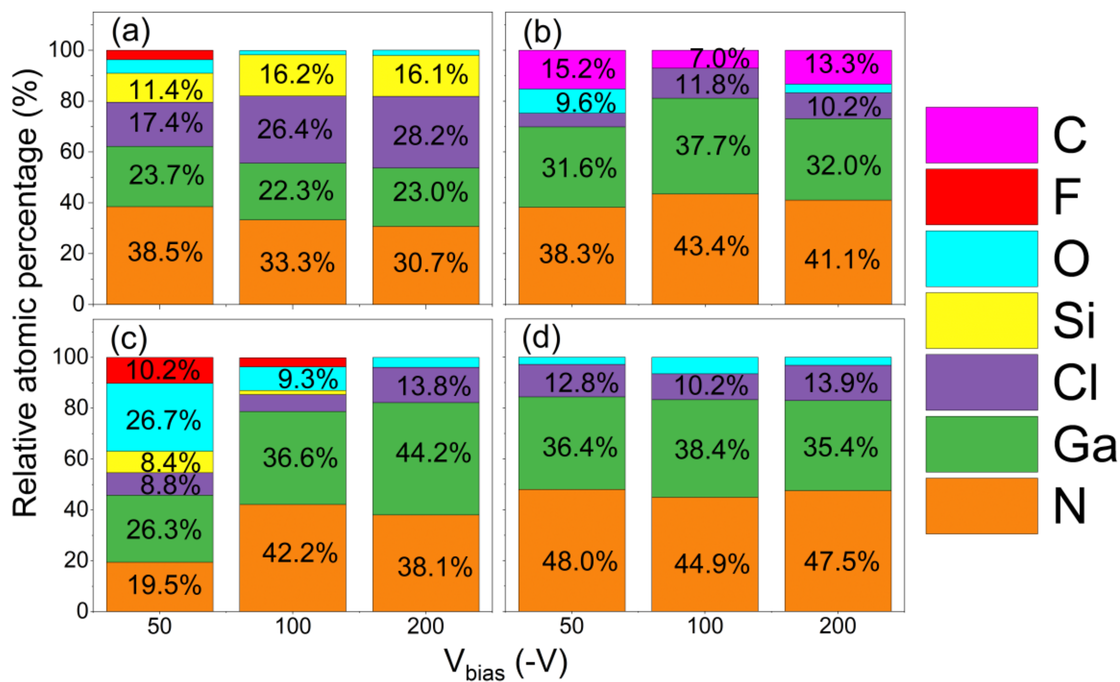

Figure 3. XPS surface composition (take off angle = 14°) of (a) GaN on Si (b) GaN on photoresist (c) GaN on SiO_2 (d) GaN on Si_3N_4 according to the bias potential.